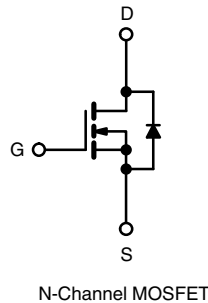
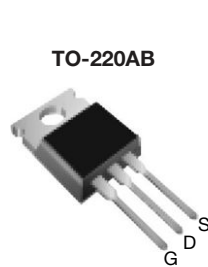


Power MOSFET

| PRODUCT SUMMARY | | |
|---------------------------|-----------------|-----|
| V_{DS} (V) | 400 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10$ V | 1.0 |
| Q_g (Max.) (nC) | 22 | |
| Q_{gs} (nC) | 5.8 | |
| Q_{gd} (nC) | 9.3 | |
| Configuration | Single | |



FEATURES

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{oss} Specified
- Compliant to RoHS Directive 2002/95/EC


RoHS*
COMPLIANT

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

TYPICAL SMPS TOPOLOGIES

- Single Transistor Flyback Xfmr. Reset
- Single Transistor Forward Xfmr. Reset (Both US Line Input Only)

| ORDERING INFORMATION | |
|----------------------|-------------|
| Package | TO-220AB |
| Lead (Pb)-free | IRF730APbF |
| | SiHF730A-E3 |
| SnPb | IRF730A |
| | SiHF730A |


| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | | |
|---|------------------|----------------|------------------|------|----------|
| PARAMETER | SYMBOL | | LIMIT | UNIT | |
| Drain-Source Voltage | V_{DS} | | 400 | V | |
| Gate-Source Voltage | V_{GS} | | ± 30 | | |
| Continuous Drain Current | V_{GS} at 10 V | $T_C = 25$ °C | 5.5 | A | |
| | | $T_C = 100$ °C | 3.5 | | |
| Pulsed Drain Current ^a | I_{DM} | | 22 | | |
| Linear Derating Factor | | | 0.6 | W/°C | |
| Single Pulse Avalanche Energy ^b | E_{AS} | | 290 | mJ | |
| Repetitive Avalanche Current ^a | I_{AR} | | 5.5 | A | |
| Repetitive Avalanche Energy ^a | E_{AR} | | 7.4 | mJ | |
| Maximum Power Dissipation | $T_C = 25$ °C | | P_D | 74 | W |
| Peak Diode Recovery dV/dt^c | | | dV/dt | 4.6 | V/ns |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | | - 55 to + 150 | °C | |
| Soldering Recommendations (Peak Temperature) | for 10 s | | 300 ^d | | |
| Mounting Torque | 6-32 or M3 screw | | | 10 | lbf · in |
| | | | | 1.1 | N · m |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25$ °C, $L = 19$ mH, $R_g = 25$ Ω , $I_{AS} = 5.5$ A (see fig. 12).
- $I_{SD} \leq 5.5$ A, $dI/dt \leq 90$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | |
|-------------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 1.70 | °C/W |
| Case-to-Sink, Flat, Greased Surface | R_{thCS} | 0.50 | - | |
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|---|-----------------------|--|---|------|-----------|---------------|----|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 400 | - | - | V | |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | - | 0.5 | - | V/°C | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2.0 | - | 4.5 | V | |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 30\text{ V}$ | - | - | ± 100 | nA | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$ | - | - | 25 | μA | |
| | | $V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | - | - | 250 | | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 3.3\text{ A}^b$ | - | - | 1.0 | Ω | |
| Forward Transconductance | g_{fs} | $V_{DS} = 50\text{ V}, I_D = 3.3\text{ A}$ | 3.1 | - | - | S | |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5 | - | 600 | - | pF | |
| Output Capacitance | C_{oss} | | - | 103 | - | | |
| Reverse Transfer Capacitance | C_{rss} | | - | 4.0 | - | | |
| Output Capacitance | C_{oss} | $V_{GS} = 0\text{ V}$ | $V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$ | - | 890 | - | |
| Effective Output Capacitance | $C_{oss\text{ eff.}}$ | | $V_{DS} = 320\text{ V}, f = 1.0\text{ MHz}$ | - | 30 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ | $V_{DS} = 0\text{ V to } 320\text{ V}^c$ | - | 45 | - | |
| Gate-Source Charge | Q_{gs} | | $I_D = 3.5\text{ A}, V_{DS} = 320\text{ V}$ see fig. 6 and 13 ^b | - | - | 22 | nC |
| Gate-Drain Charge | Q_{gd} | | | - | - | 5.8 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 200\text{ V}, I_D = 3.5\text{ A}$ $R_g = 12\text{ }\Omega, R_D = 57\text{ }\Omega,$ see fig. 10 ^b | - | 10 | - | ns | |
| Rise Time | t_r | | - | 22 | - | | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 20 | - | | |
| Fall Time | t_f | | - | 16 | - | | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 5.5 | A | |
| Pulsed Diode Forward Current ^a | I_{SM} | | - | - | 22 | | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 5.5\text{ A}, V_{GS} = 0\text{ V}^b$ | - | - | 1.6 | V | |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = 3.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$ | - | 370 | 550 | ns | |
| Body Diode Reverse Recovery Charge | Q_{rr} | | - | 1.6 | 2.4 | μC | |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

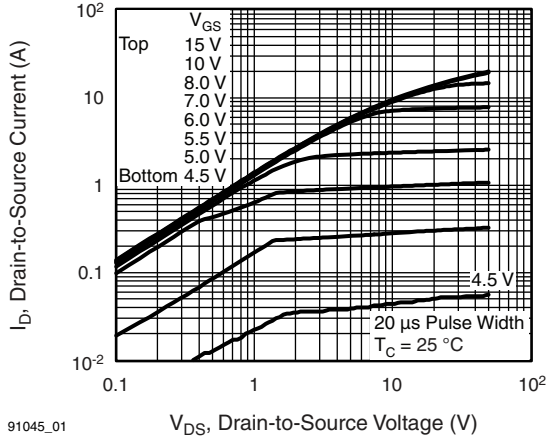


Fig. 1 - Typical Output Characteristics

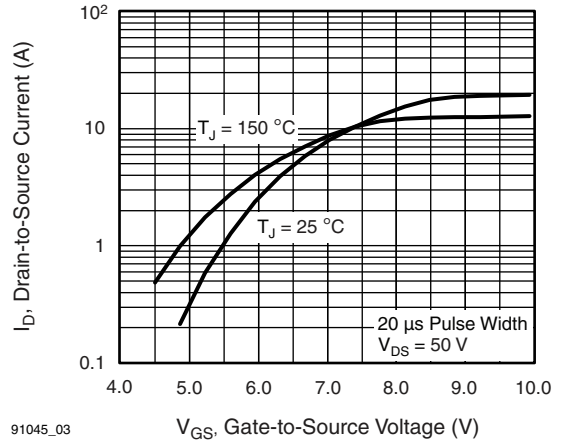


Fig. 3 - Typical Transfer Characteristics

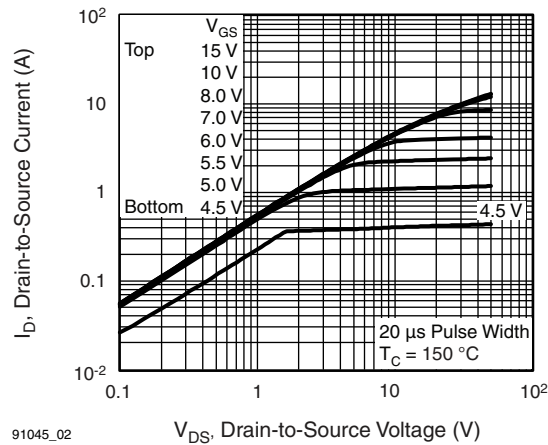


Fig. 2 - Typical Output Characteristics

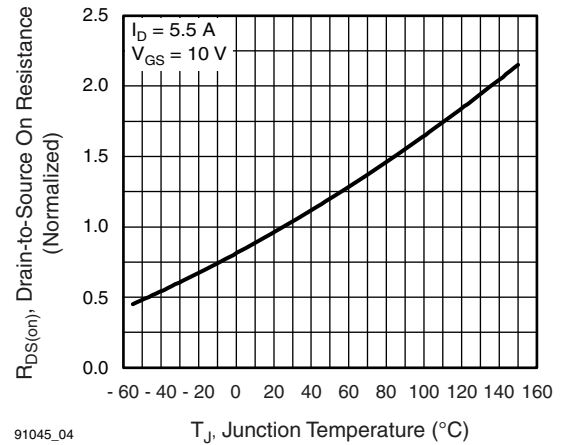


Fig. 4 - Normalized On-Resistance vs. Temperature

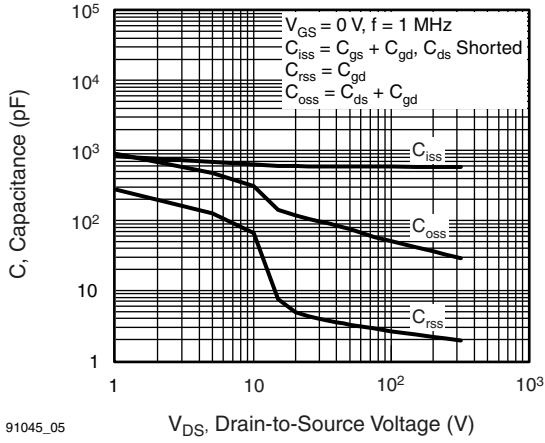


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

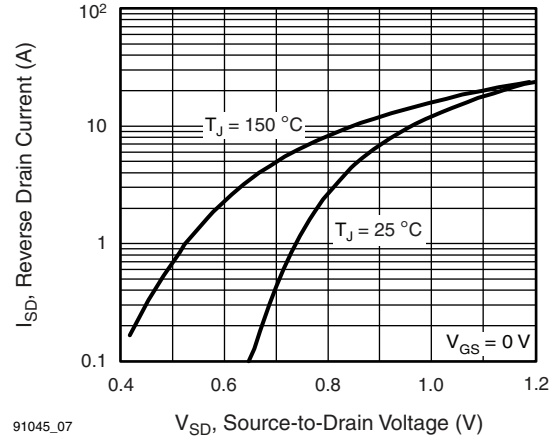


Fig. 7 - Typical Source-Drain Diode Forward Voltage

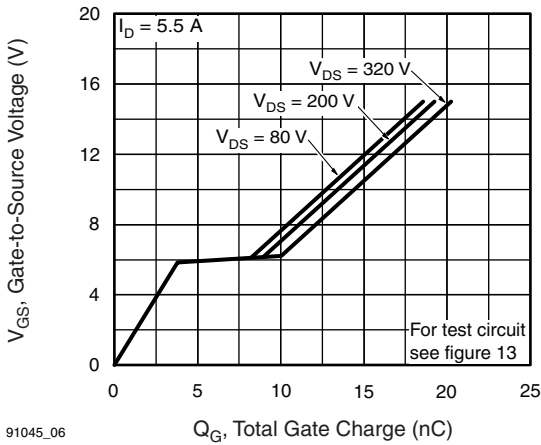


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

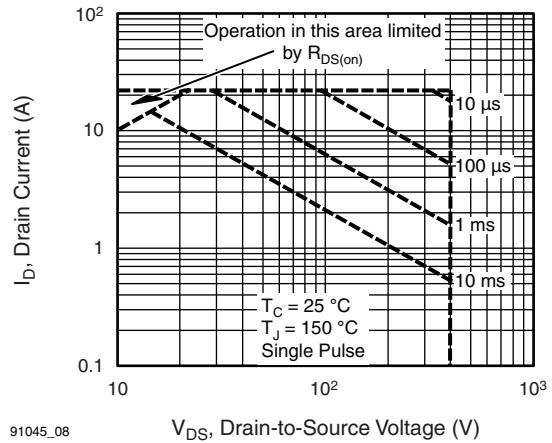
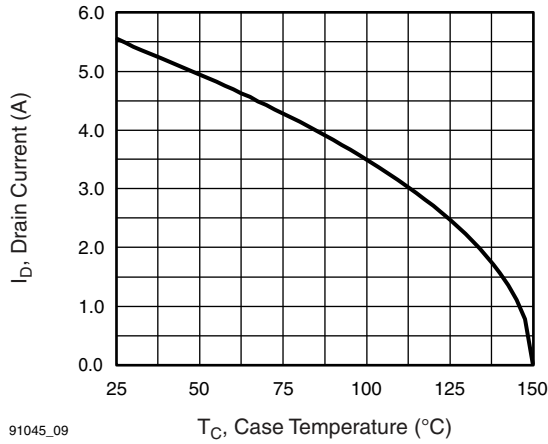


Fig. 8 - Maximum Safe Operating Area



91045_09

Fig. 9 - Maximum Drain Current vs. Case Temperature

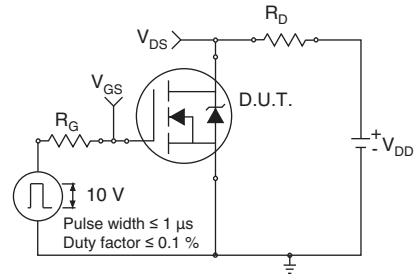


Fig. 10a - Switching Time Test Circuit

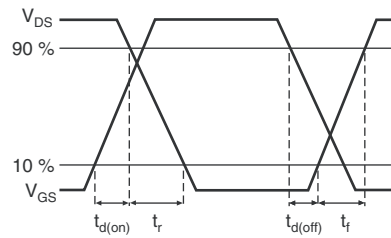
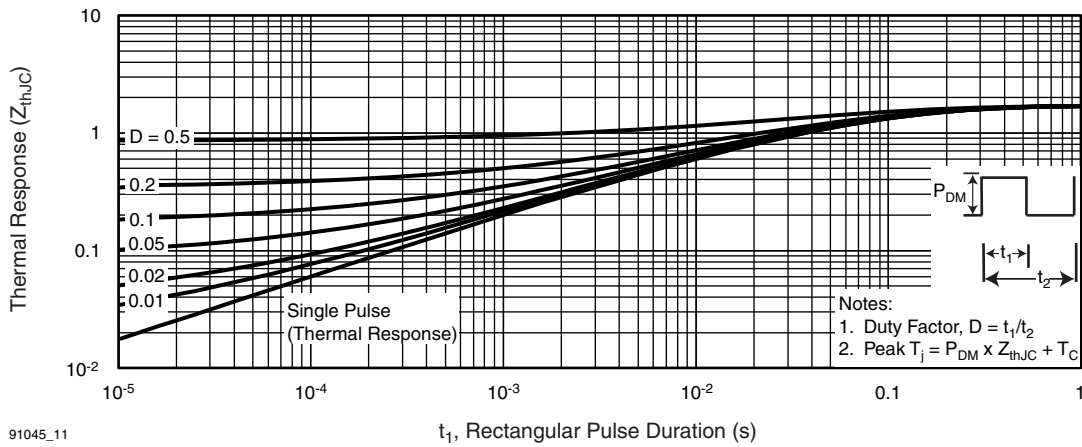


Fig. 10b - Switching Time Waveforms



91045_11

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

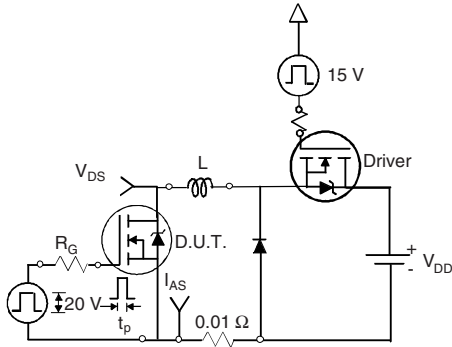


Fig. 12a - Unclamped Inductive Test Circuit

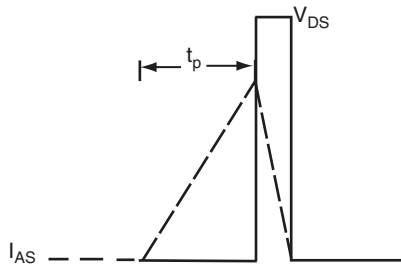
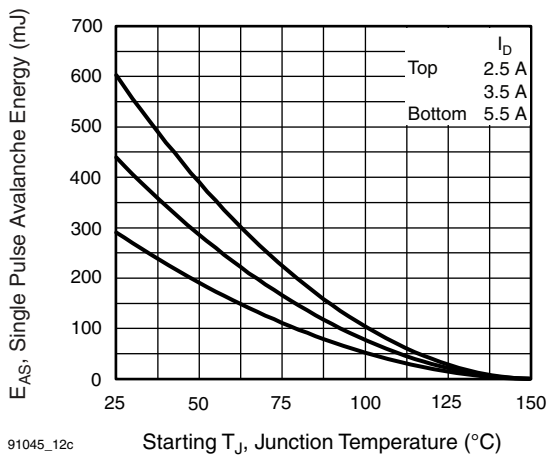
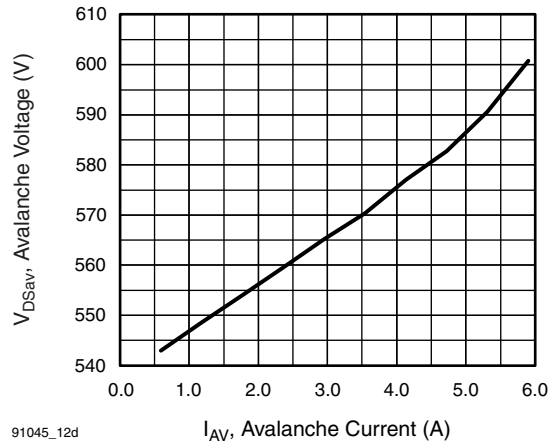


Fig. 12b - Unclamped Inductive Waveforms



91045_12c

Fig. 12c - Maximum Avalanche Energy vs. Drain Current



91045_12d

Fig. 12d - Typical Drain Source Voltage vs. Avalanche Current

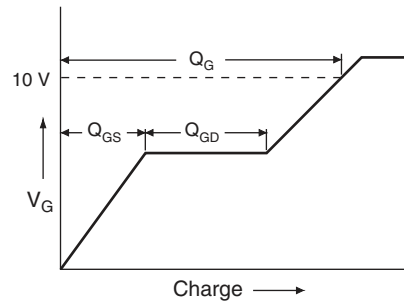


Fig. 13a - Basic Gate Charge Waveform

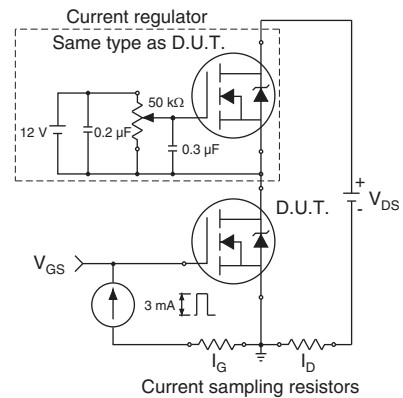
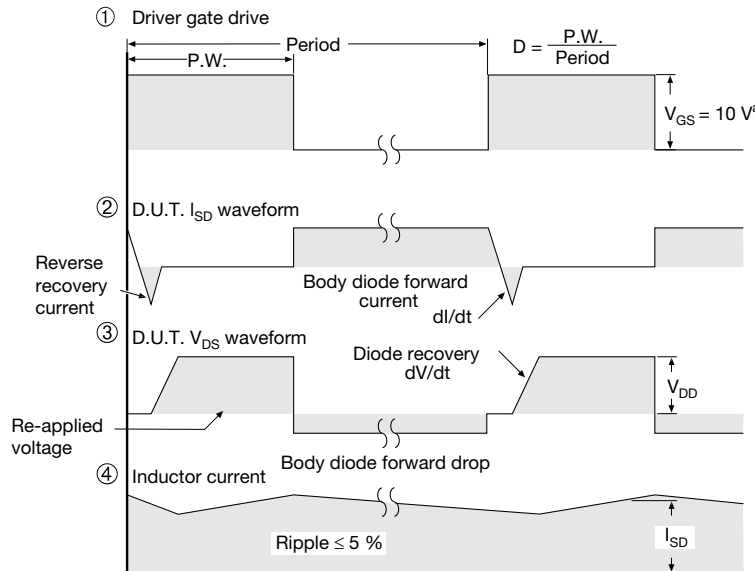
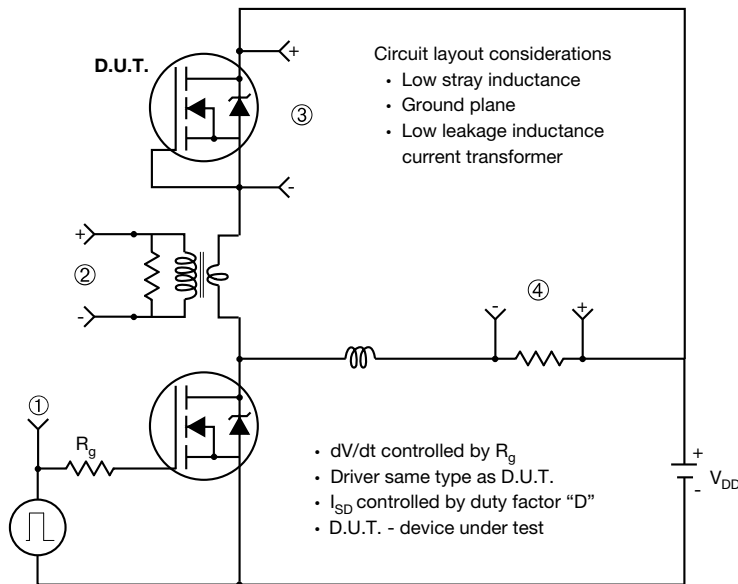


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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TO-220-1



| DIM. | MILLIMETERS | | INCHES | |
|-----------------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.14 | 4.70 | 0.163 | 0.185 |
| b | 0.69 | 1.02 | 0.027 | 0.040 |
| b(1) | 1.14 | 1.73 | 0.045 | 0.068 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.33 | 15.85 | 0.564 | 0.624 |
| E | 9.96 | 10.52 | 0.392 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 0.43 | 1.40 | 0.017 | 0.055 |
| H(1) | 6.10 | 6.48 | 0.240 | 0.255 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.36 | 14.40 | 0.526 | 0.567 |
| L(1) | 3.33 | 4.04 | 0.131 | 0.159 |
| $\varnothing P$ | 3.53 | 3.94 | 0.139 | 0.155 |
| Q | 2.59 | 3.00 | 0.102 | 0.118 |

ECN: X15-0003-Rev. A, 19-Jan-15
DWG: 6031

Notes

- M^* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM
- Outline conforms to JEDEC® outline TO-220AB with exception of dimension F



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